



PJD60N06

60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

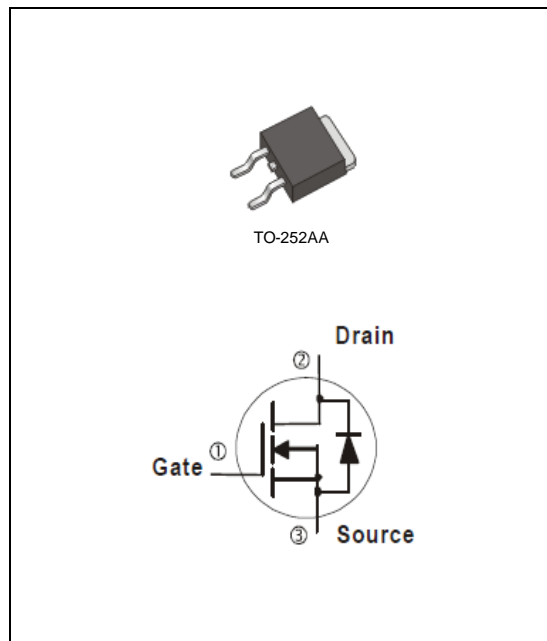
60 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@30A < 10m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.. (Halogen Free)

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C=25^\circ C$	I_D	60	A
	$T_C=100^\circ C$		38	
Pulsed Drain Current (Note 1)	$T_C=25^\circ C$	I_{DM}	240	
Power Dissipation	$T_C=25^\circ C$	P_D	72	W
	$T_C=100^\circ C$		29	
Continuous Drain Current	$T_A=25^\circ C$	I_D	10	A
	$T_A=70^\circ C$		8	A
Power Dissipation	$T_A=25^\circ C$	P_D	2.0	W
Power Dissipation	$T_A=70^\circ C$		1.3	
Single Pulse Avalanche Energy (Note 6)		E_{AS}	180	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ C$
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	1.7	$^\circ C/W$
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature



PJD60N06

Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2.0	2.8	3.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =30A	-	8.4	10	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic (Note 7)						
Total Gate Charge	Q _g	V _{DS} =48V, I _D =25A, V _{GS} =10V (Note 1,2)	-	52	-	nC
Gate-Source Charge	Q _{gs}		-	11	-	
Gate-Drain Charge	Q _{gd}		-	15	-	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	2904	-	pF
Output Capacitance	C _{oss}		-	241	-	
Reverse Transfer Capacitance	C _{rss}		-	112	-	
Turn-On Delay Time	td _(on)	V _{DD} =30V, I _D =30A, V _{GS} =10V, R _G =3.3Ω (Note 1,2)	-	18	-	ns
Turn-On Rise Time	t _r		-	48	-	
Turn-Off Delay Time	td _(off)		-	54	-	
Turn-Off Fall Time	t _f		-	18	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	60	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	0.7	1.2	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature T_J(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J = 25°C.
4. The maximum current rating is package limited.
5. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. The test condition is L=0.1mH, I_{AS}=60A, V_{DD}=25V, V_{GS}=10V
7. Guaranteed by design, not subject to production testing.



PJD60N06

TYPICAL CHARACTERISTIC CURVES

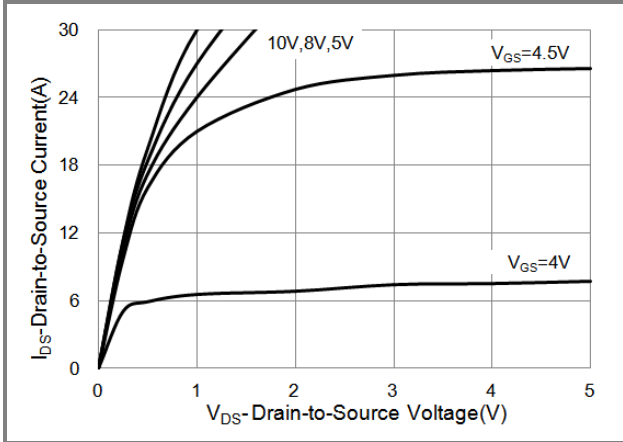


Fig.1 Output Characteristics

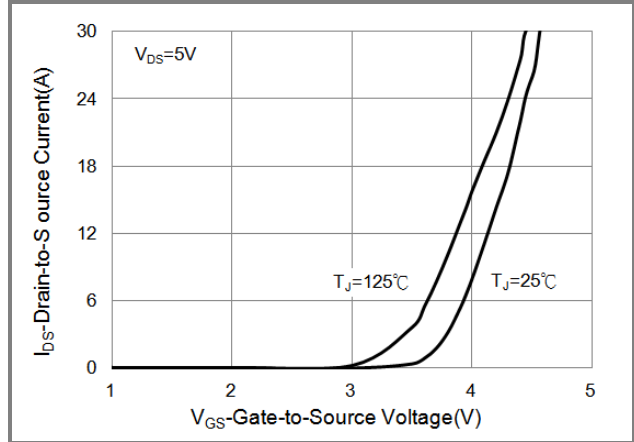


Fig.2 Transfer Characteristics

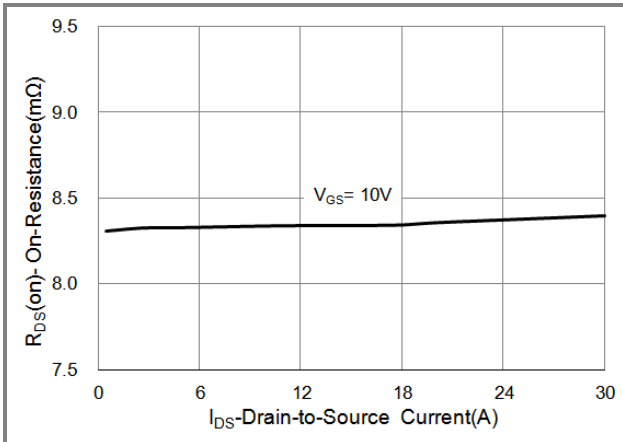


Fig.3 On-Resistance vs. Drain Current

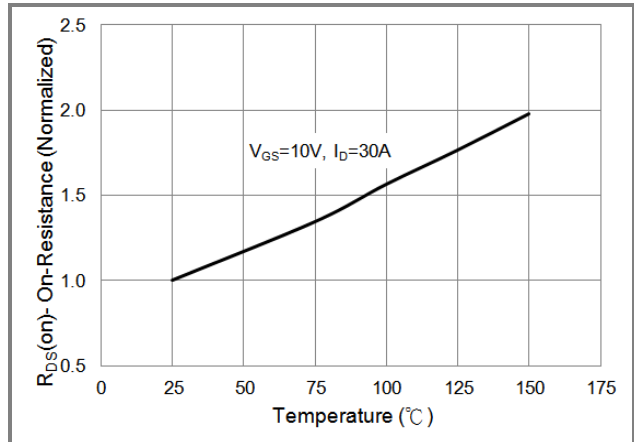


Fig.4 On-Resistance vs. Junction temperature

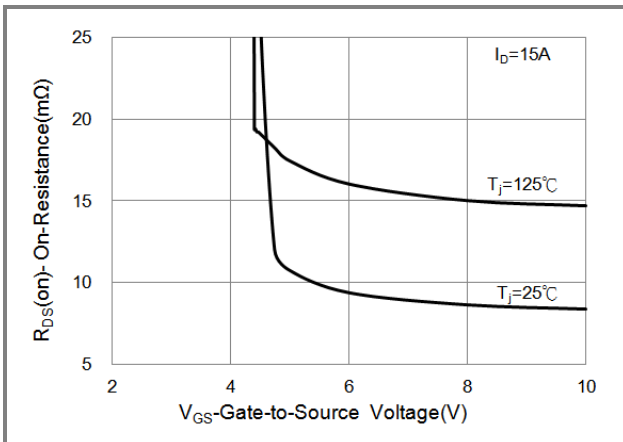


Fig.5 On-Resistance Variation with VGS.

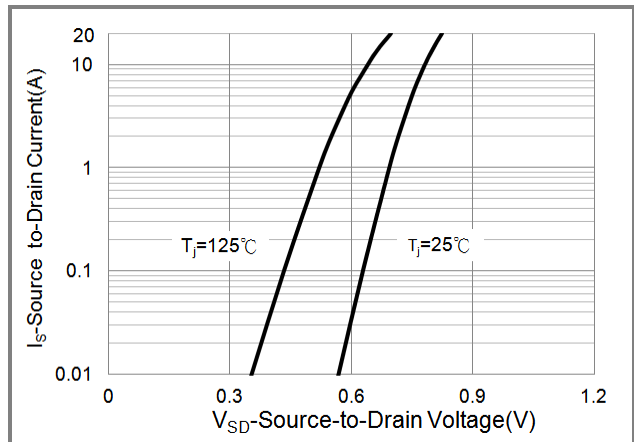


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

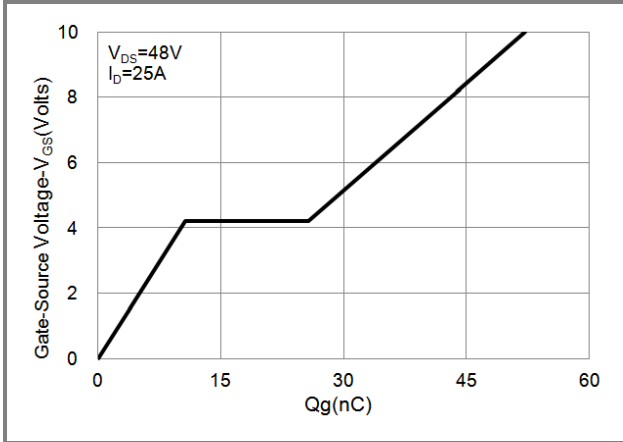


Fig.7 Gate-Charge Characteristics

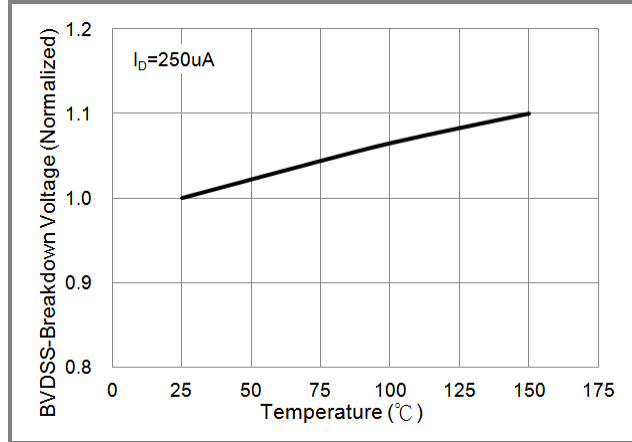


Fig.8 Breakdown Voltage Variation vs. Temperature

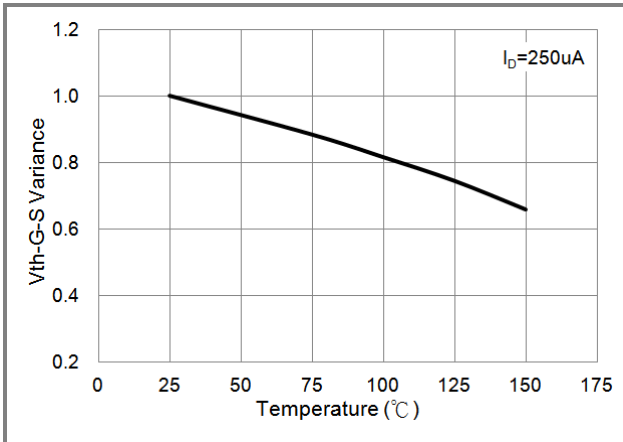


Fig.9 Threshold Voltage Variation with Temperature

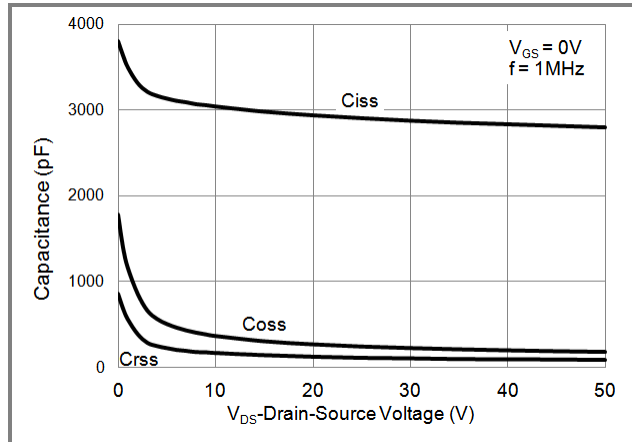


Fig.10 Capacitance vs. Drain-Source Voltage

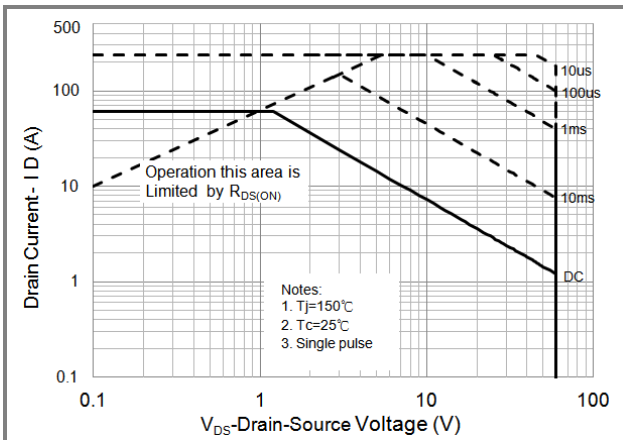


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

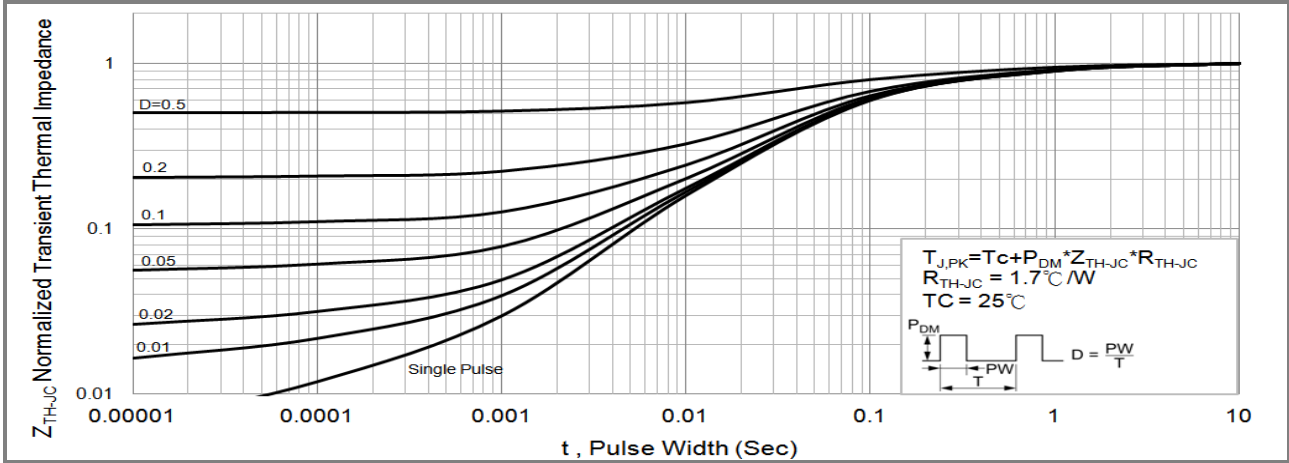
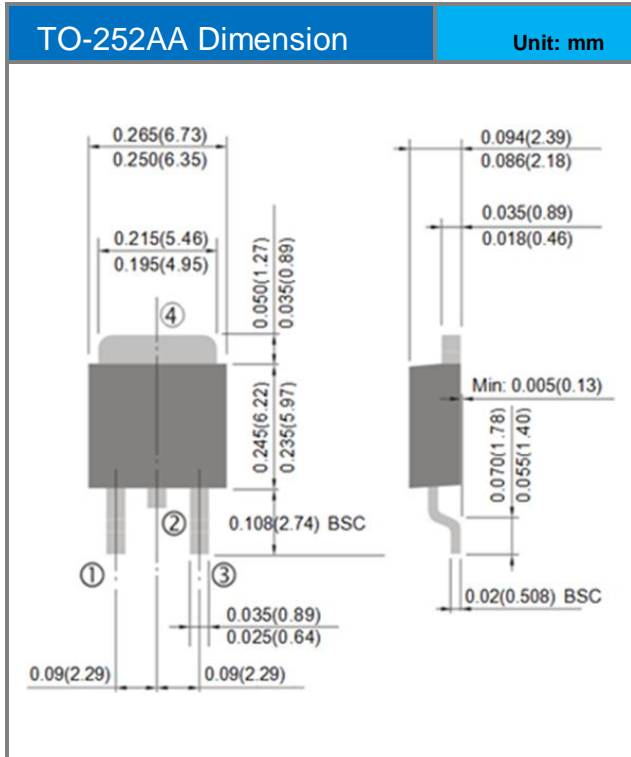


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



PJD60N06

Packaging Information



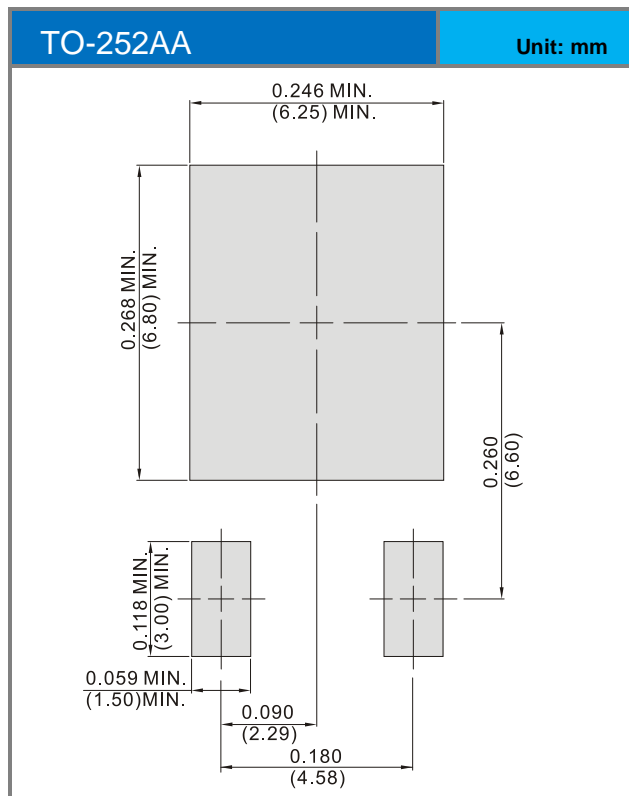


PJD60N06

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD60N06_L2_00001	TO-252AA	3,000pcs / 13" reel	D60N06	Halogen free

MOUNTING PAD LAYOUT





PJD60N06

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